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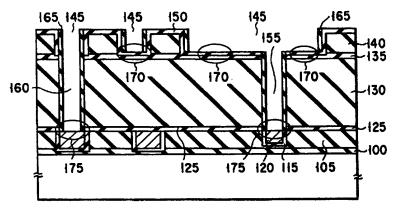
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(54) Method of manufacturing a semiconductor device of multilayer wire structure

(57) In a method of manufacturing a semiconductor device, when a copper diffusion preventing film portion (165) on the connecting hole bottom portion (145,155) is to be removed, a film thickness of other portion of the copper diffusion preventing film (165) not to be removed is more thickly formed than that of the to-be-removed copper diffusion preventing film portion on the connecting hole bottom portion, thereby only the copper diffusion

sion preventing film portion to be removed can be removed. The method can extend a durable length of time of a wire and can reduce a resistance of the metal wires in a connecting hole bottom portion by removing a copper diffusion preventing film (165) on the bottom portion of the connecting hole (145,155).



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EUROPEAN SEARCH REPORT

Application Number EP 97 10 5040

Category	Citation of document with indicated of relevant passages		Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
Ą	US 5 281 850 A (KANAMO * column 2, line 50 - * figures 1A-1F *	RI JUN)	1-30	H01L21/768 H01L23/522
A	EP 0 571 108 A (SGS TH MICROELECTRONICS) * column 1, line 53 - * figures 1-4 *		1-30	
A	CA 2 082 771 A (HO VU (CA); EMESH ISMAIL T (
				TECHNICAL FIELDS SEARCHED (Int.Cl.6)
				H01L
	The present search report has been			
Place of search THE HAGUE		Date of completion of the search 27 April 1998	ScI	Examiner huermans, N
X:pai Y:pai doo	CATEGORY OF CITED DOCUMENTS rticularly relevant if taken alone rticularly relevant if combined with another cument of the same category thrological background	T: theory or princ E: earlier patent after the filing D: document cite L: document cite	iple underlying the document, but pub date d in the application d for other reasons	invention dished on, or